

# InAsSb photovoltaic detector

P11120-201



**High-speed response and high sensitivity in the 5  $\mu\text{m}$  spectral band**  
**Thermoelectrically cooled infrared detector with no liquid nitrogen required**

The P11120-201 is an infrared detector that provides high sensitivity in the 5  $\mu\text{m}$  spectral band due to our unique crystal growth technology. The InAsSb photovoltaic detector has a PN junction that ensures high-speed response and high reliability. Typical applications include gas analysis such as CO<sub>2</sub>, SO<sub>x</sub>, CO and NO<sub>x</sub>. Unlike the P11120-901 metal dewar type detector, the P11120-201 is easy to use as it uses a compact package (TO-8) not requiring liquid nitrogen.

## Features

- High-speed response
- High sensitivity
- High reliability
- Compact, thermoelectrically cooled TO-8 package
- Environment-friendly due to use of InAsSb
- Suitable for detecting infrared rays emitted from QCL

## Applications

- Gas analysis
- Radiation thermometers
- Thermal imaging
- Remote sensing
- FTIR
- Spectrophotometry

## Options (sold separately)

- Heatsink for two-stage TE-cooled type A3179-01
- Temperature controller C1103-04
- Infrared detector module with preamp C4159-07

## Structure

Parameter	Specification	Unit
Window material	Sapphire	-
Package	TO-8	-
Cooling	Two-stage TE-cooled	-
Photosensitive area	$\phi 1.0$	mm

## Absolute maximum ratings

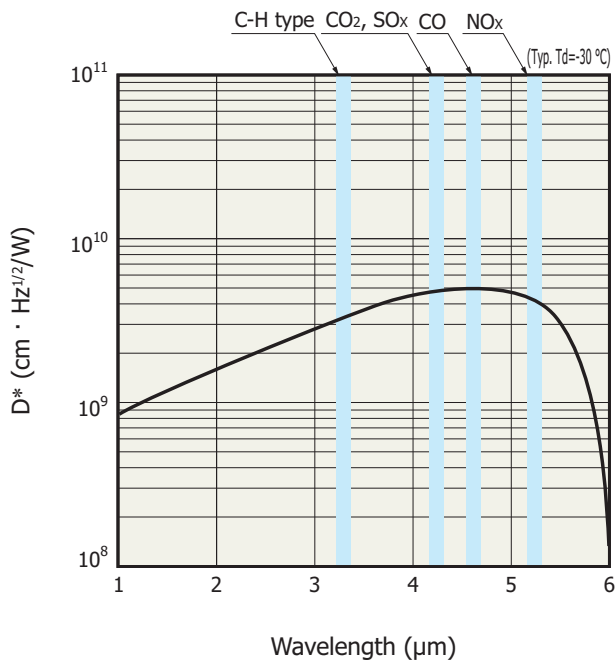
Parameter	Symbol	Value	Unit
Thermistor power dissipation	-	0.2	mW
Reverse voltage	V <sub>R</sub>	0.1	V
Operating temperature	T <sub>opr</sub>	-40 to +60	°C
Storage temperature	T <sub>stg</sub>	-55 to +60	°C

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

**Electrical and optical characteristics (Td=-30 °C)**

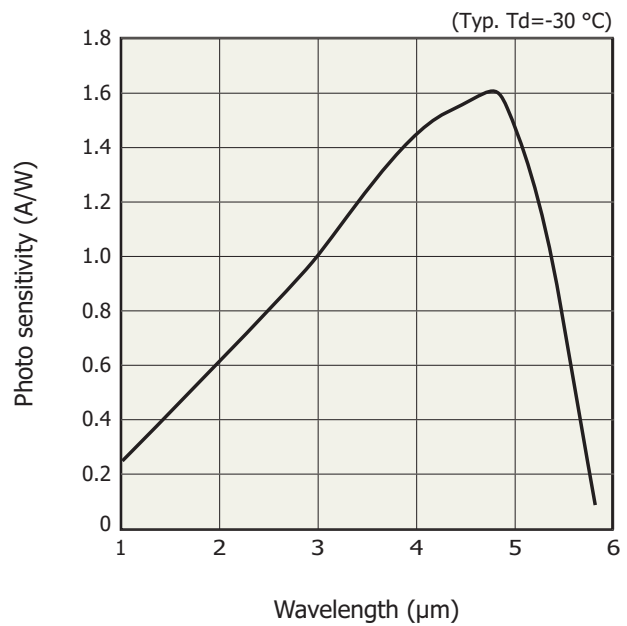
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Peak sensitivity wavelength	$\lambda_p$		4.0	4.9	-	$\mu\text{m}$
Cutoff wavelength	$\lambda_c$		5.6	5.9	-	$\mu\text{m}$
Photo sensitivity	S	$\lambda = \lambda_p$	0.8	1.6	-	A/W
Shunt resistance	Rsh	$V_R = 10 \text{ mV}$	10	13	-	$\Omega$
Detectivity	$D^*$	$(\lambda_p, 600, 1)$	$3.5 \times 10^9$	$5.0 \times 10^9$	-	$\text{cm} \cdot \text{Hz}^{1/2} / \text{W}$
Noise equivalent power	NEP	$\lambda = \lambda_p$	-	$1.8 \times 10^{-11}$	$2.5 \times 10^{-11}$	$\text{W} / \text{Hz}^{1/2}$
Rise time	tr	$V_R = 0 \text{ V}, R_L = 50 \Omega$ 0 to 63%	-	0.4	-	$\mu\text{s}$

**Spectral response ( $D^*$ )**



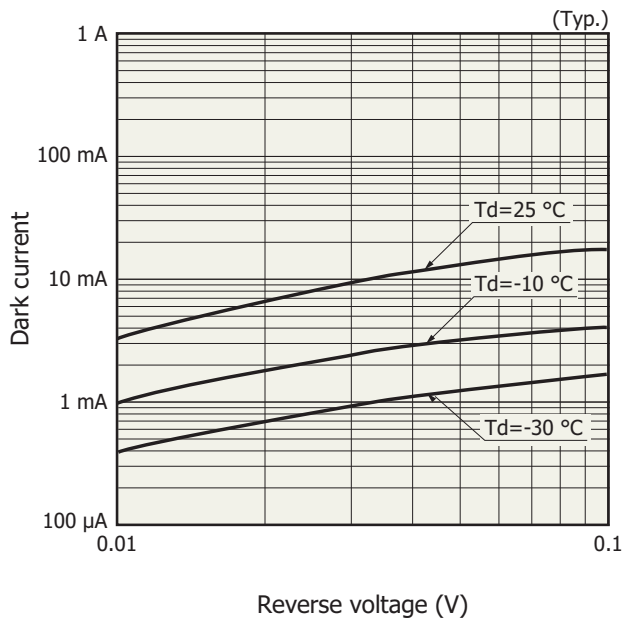
KIRDB0452EA

**Spectral response**



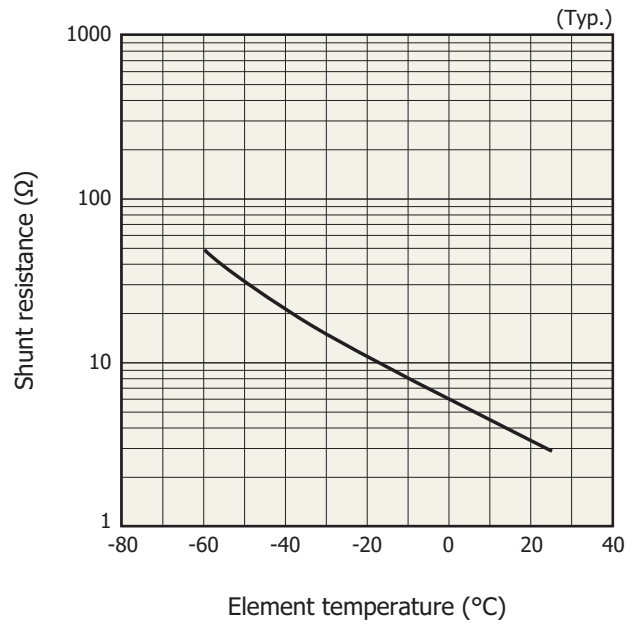
KIRDB0453EA

**Dark current vs. reverse voltage**



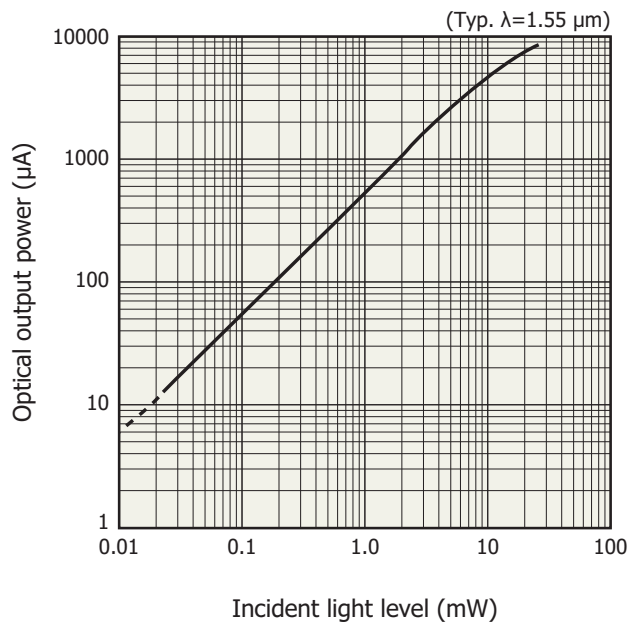
KIRDB0454EA

**Shunt resistance vs. element temperature**



KIRDB0455EA

**Linearity**

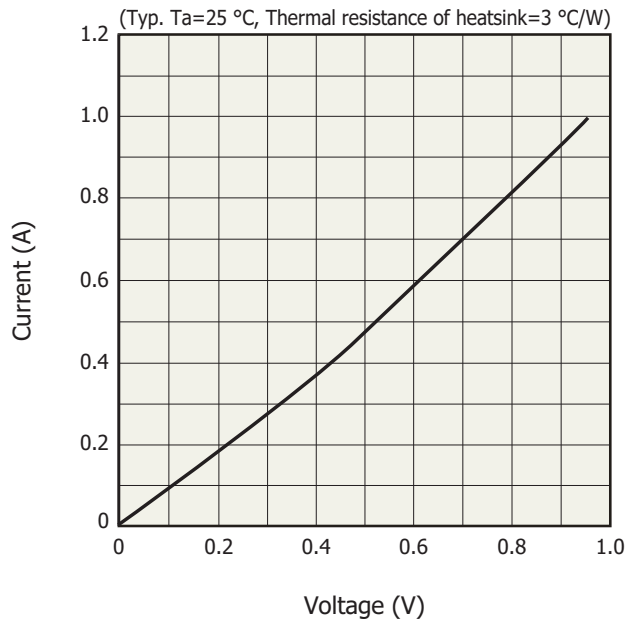


KIRDB0456EA

▣ Specifications of two-stage TE-cooler (Ta=25 °C)

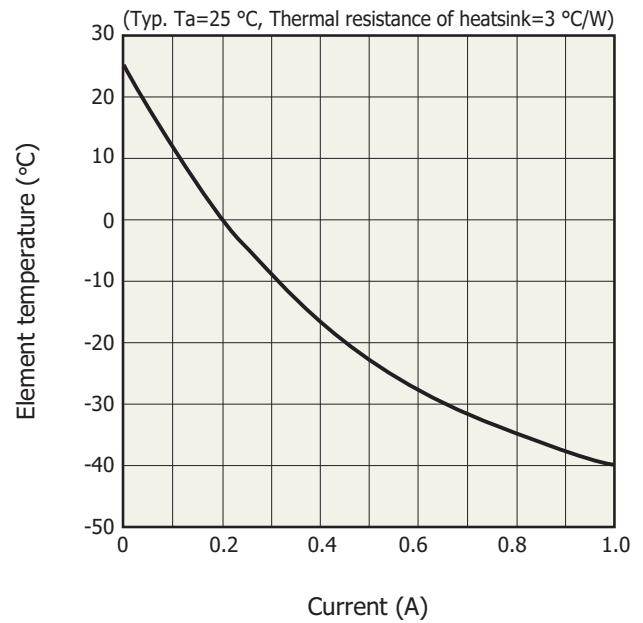
Parameter	Symbol	Min.	Typ.	Max.	Unit
Allowable current	Ic	-	-	1.0	A
Allowable voltage	Vc	-	-	0.95	V
Thermistor resistance	Rth	8.1	9.0	9.9	kΩ
Thermistor power dissipation	Pth	-	-	0.2	mW

▣ Current vs. voltage of TE-cooled type



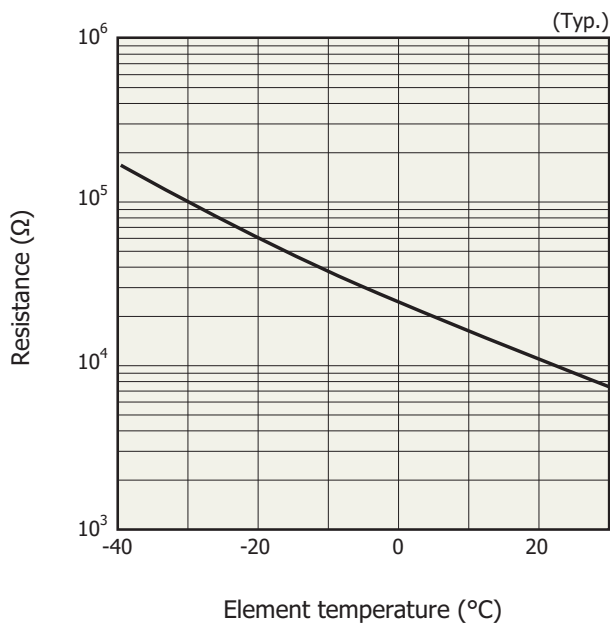
KIRDB0459EA

▣ Cooling characteristics of TE-cooled type



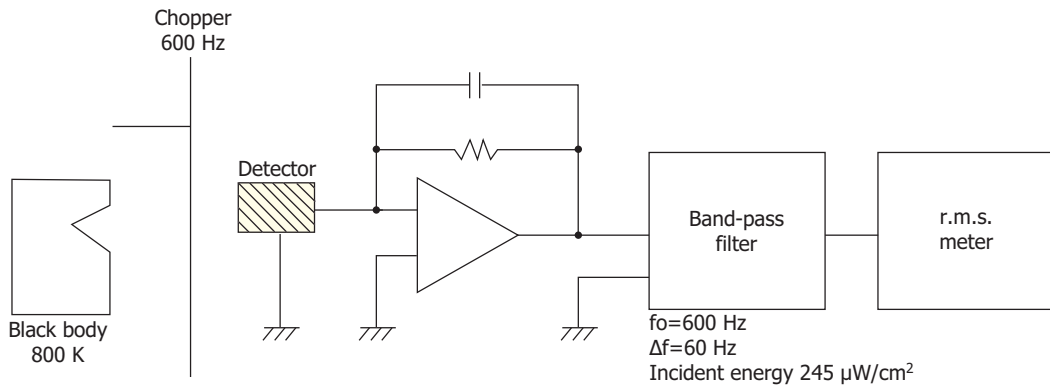
KIRDB0464EA

▣ Thermistor temperature characteristic



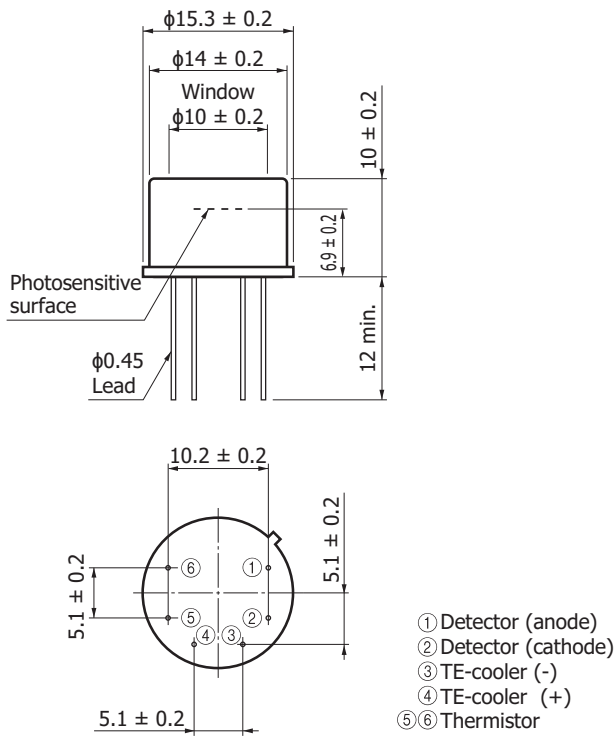
KIRDB0116EA

Measurement circuit example



KIRDC0094EA

Dimensional outline (unit: mm)



KIRDA0212EA

## Related information

[www.hamamatsu.com/sp/ssd/doc\\_en.html](http://www.hamamatsu.com/sp/ssd/doc_en.html)

### ■ Precautions

- Disclaimer
- Metal, ceramic, plastic products

### ■ Technical information

- Infrared detectors

Information described in this material is current as of May, 2015.

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